Product data sheet

1. General description

Ultrafast power diode in a SMC package.

2. Features and benefits

- Fast switching
- SMC package
- High voltage capability
- · Low forward voltage drop
- Low leakage current
- · Low thermal resistance
- Soft recovery characteristic

3. Applications

- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- · use in switching power supplies, inverters and as free wheeling diodes
- · High frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values	Unit
Absolute	maximum rating			
V_{RRM}	repetitive peak reverse voltage		600	V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; $T_{lead} \le 95$ °C; Fig. 1; Fig. 2; Fig. 3	8	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{lead} ≤ 95 °C; square-wave pulse	16	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	180	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	200	Α

MUR860

Ultrafast power diode

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		v 14 .
2	Α	anode	1 2	K — A 001aaa020

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
MUR860	SMC	MUR860J	Reel	3000	SMCS	16-Aug-2017

7. Marking

Table 4. Marking codes

Type number	Marking codes
MUR860	860

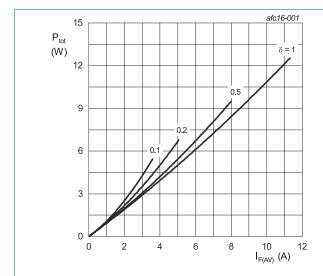
Ultrafast power diode

8. Limiting values

Table 5. Limiting values

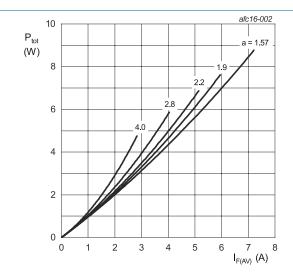
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; T _{lead} ≤ 95 °C; Fig. 1; Fig. 2; Fig. 3	8	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{lead} ≤ 95 °C; square-wave pulse	16	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	180	Α
		$t_p = 8.3 \text{ ms; } T_{j(init)} = 25 \text{ °C; sine-wave pulse}$	200	Α
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C



$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 0.918 \text{ V; } R_s = 0.0168 \text{ } \Omega \end{split}$$

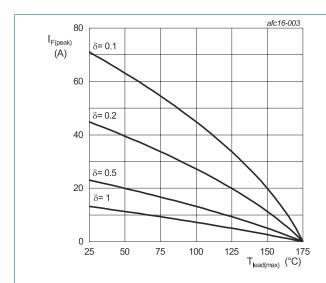
Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

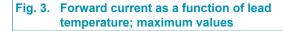


a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 0.918 V; R_s = 0.0168 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

Ultrafast power diode





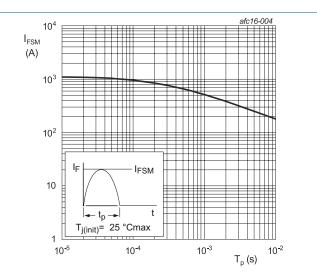


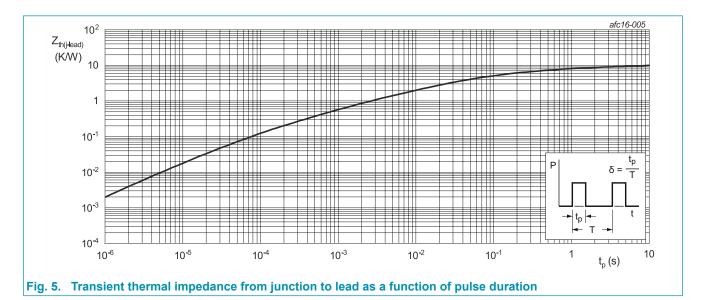
Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

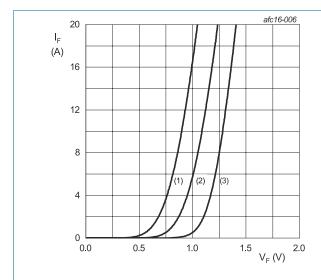
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	<u>Fig. 5</u>	-	-	10	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	75	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics			·		
V_{F}	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	-	1.25	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>	-	-	1.05	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	400	μA
Dynamic	characteristics					
Q _r	reverse charge	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/us};$ $T_j = 25 \text{ °C}; Fig. 7$	-	494	-	nC
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/us};$ $T_j = 125 \text{ °C}; Fig. 7$	-	983	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/us};$ $T_j = 25 \text{ °C}; Fig. 7$	-	66	90	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/us};$ $T_j = 25 \text{ °C}; Fig. 7$	-	93	-	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/us};$ $T_j = 125 \text{ °C}; Fig. 7$	-	130	-	ns
I _{RM}	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/us};$ $T_j = 25 \text{ °C}; Fig. 7$	-	11	-	А
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/us};$ $T_i = 125 \text{ °C}; Fig. 7$	-	15	-	А



 V_o = 0.918 V; R_s = 0.0168 Ω

(1) $T_j = 150 \,^{\circ}\text{C}$; typical values (2) $T_j = 150 \,^{\circ}\text{C}$; maximum values (3) $T_j = 25 \,^{\circ}\text{C}$; maximum values

Fig. 6. Forward current as a function of forward voltage

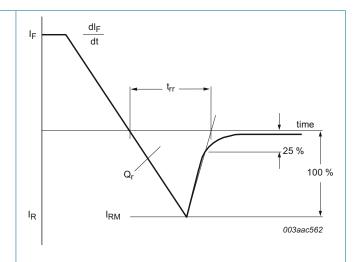
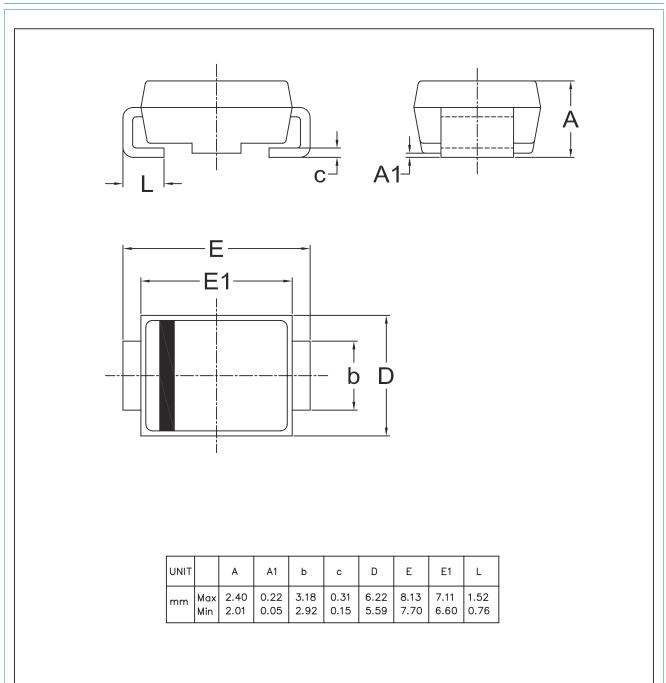


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



Remark: Dimensions D and E1 do not include mold flash.

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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For more information, please visit: http://www.ween-semi.com
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